

Rev. 1.1 — 28 February 2025

Product data sheet

1. General description

The NGW40T65M3DFP is a robust Insulated-Gate Bipolar Transistor (IGBT) featuring third-generation technology. It combines carrier stored trench-gate and field-stop (FS) structures. The NGW40T65M3DFP is rated to 175 °C with optimized IGBT turn-off losses, and has a short-circuit withstand time of 5 μs . This hard-switching 650 V, 40 A IGBT is optimized for high-voltage, high-frequency industrial power inverter applications and servo motor drive applications.

2. Features

- Device current is rated at 40 A
- Low conduction and switching losses
- Stable and tight parameters for easy parallel operation
- Maximum junction temperature 175 °C
- Fully rated and soft fast reverse recovery diode
- 5 μs short circuit withstand time
- HV-H3TRB qualified

3. Applications

- Motor drives for industrial and consumer appliances
 - Servo motors operating between 5-20 kW (up to 20 kHz) for robotics, elevators, operating grippers, in-line manufacturing, etc.
- Power inverters, such as
 - · Uninterruptible Power Supply (UPS) inverter
 - EV charging converter
- · Induction heating
- Welding

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CES}	collector-emitter voltage	T _{vj} = 25 °C	-	650	V
T_{vj}	operating junction temperature		-40	175	°C
t _{sc}	short circuit withstand time	V _{GE} = 15 V ; V _{CC} = 400 V; T _{vj} ≤ 150 °C	-	5	μs



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	
2	С	collector		C
3	Е	emitter		
mb	С	mounting base; connected to collector		G E aaa-036518

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NGW40T65M3DFP	TO-247-3L	Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247-3L	SOT429-2			

7. Limiting values

Table 4. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
IGBT					
V _{CES}	collector-emitter voltage	T _{vj} = 25 °C	-	650	V
I _C	collector current [1] T _c = 25 °C	-	72	А
		T _c = 100 °C	-	48	А
I _{CRM}	repetitive peak collector [2 current]	-	120	Α
t _{sc}	short circuit withstand time [3	$V_{GE} = 15 \text{ V}; V_{CC} = 400 \text{ V}; T_{vj} \le 150 \text{ °C}$	-	5.0	μs
V_{GE}	gate-emitter voltage		-20	20	V
P _{tot}	total power dissipation	T _c = 25 °C	-	283	W
		T _c = 100 °C	-	142	W
T_{vj}	operating junction temperature		-40	175	°C
T _{stg}	storage temperature		-55	150	°C
T _{solder}	soldering temperature		-	260	°C
Diode					
I _F	diode forward current [1] T _c = 25 °C	-	80	Α
		T _c = 100 °C	-	49	Α
I _{FRM}	repetitive peak forward [2 current]	-	120	А

Value is limited by bondwire and $T_{vj(max)}$. Time duration is limited by $T_{vj(max)}$. Short circuit cycles \leq 1000, time between tests \geq 1 s.

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
M	mounting torque, M3 screw		-	0.6	-	Nm
R _{th(j-c)}	thermal resistance from junction to case	IGBT	-	0.45	0.53	K/W
		diode	-	0.71	0.84	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	-	40	K/W

9. Electrical characteristics

Table 6. Characteristics

All values at T_{vj} = 25 °C, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _{(BR)CES}	collector-emitter breakdown voltage	$V_{GE} = 0 \text{ V}; I_{C} = 0.2 \text{ mA}$	650	-	-	V
V _{CEsat}	collector-emitter saturation	V _{GE} = 15 V; I _C = 40 A; T _{vj} = 25 °C	-	1.5	1.9	V
	voltage	V _{GE} = 15 V; I _C = 40 A; T _{vj} = 175 °C	-	1.9	-	V
V _F	diode forward voltage	V _{GE} = 0 V; I _F = 40 A; T _{vj} = 25 °C	-	1.62	2.1	V
		V _{GE} = 0 V; I _F = 40 A; T _{vj} = 175 °C	-	1.33	-	V
$V_{\text{GE(th)}}$	gate-emitter threshold voltage	$I_C = 0.4 \text{ mA}; V_{CE} = V_{GE}; T_{vj} = 25 \text{ °C}$	4.3	5	5.7	V
I _{CES}	zero gate voltage collector	V _{CE} = 650 V; V _{GE} = 0 V; T _{vj} = 25 °C	-	10	-	nA
	current	V _{CE} = 650 V; V _{GE} = 0 V; T _{vj} = 175 °C	-	0.5	-	mA
I _{GES}	gate-emitter leakage current	V _{CE} = 0 V; V _{GE} = 20 V	-	-	100	nA
g _{fs}	transconductance	V _{CE} = 20 V; I _C = 40 A; T _{vj} = 25 °C	-	20	-	S
r _g	internal gate resistor		-	1.3	-	Ω
Dynamic	characteristics					
C _{ies}	input capacitance	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz	-	2040	-	pF
C _{oes}	output capacitance		-	136	-	pF
C _{res}	reverse transfer capacitance		-	31	-	pF
Q_G	gate charge	V _{CC} = 520 V; V _{GE} = 15 V; I _C = 40 A	-	130	-	nC
L _{sCE}	internal stray inductance	measured 5 mm from case	-	7.9	-	nΗ
I _{C(sc)}	short circuit collector current	$V_{GE} = 15 \text{ V}; V_{CC} = 400 \text{ V}; t_{sc} \le 5 \mu\text{s}; T_{vj} \le 150$ ° C	-	185	-	А

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
IGBT sw	vitching characteristics, induc	ctive load					
t _{d(on)}	turn-on delay time	V _{GE} = 15/0 V; V _{CC} = 400 V;	T _{vj} = 25 °C	-	22	-	ns
		$I_C = 40 \text{ A}; R_{G(on)} = 10 \Omega;$ $R_{G(off)} = 10 \Omega;$	T _{vj} = 175 °C	-	20	-	ns
t _r	rise time	see <u>Fig. 27</u> and <u>Fig. 28</u>	T _{vj} = 25 °C	-	22	-	ns
			T _{vj} = 175 °C	-	23	-	ns
t _{d(off)}	turn-off delay time		T _{vj} = 25 °C	-	185	-	ns
			T _{vj} = 175 °C	-	220	-	ns
t _f fal	fall time		T _{vj} = 25 °C	-	13	-	ns
			T _{vj} = 175 °C	-	50	-	ns
E _{on}	turn-on switching energy		T _{vj} = 25 °C	-	1.05	-	mJ
	loss	⊣	T _{vj} = 175 °C	-	2.15	-	mJ
E _{off} turn-off switching energy			T _{vj} = 25 °C	-	0.52	-	mJ
	loss		T _{vj} = 175 °C	-	0.9	-	mJ
E _{ts}	total switching energy loss		T _{vj} = 25 °C	-	1.57	-	mJ
			T _{vj} = 175 °C	-	3.05	-	mJ
Diode sv	witching characteristics, indu	ictive load					
t _{rr}	reverse recovery time	V _R = 400 V; I _F = 40 A;	T _{vj} = 25 °C	-	55	-	ns
		di _F /dt = 1000 A/μs; see <u>Fig. 26</u>	T _{vj} = 175 °C	-	215	-	ns
Q _{rr}	reverse recovery charge	See <u>Fig. 20</u>	T _{vj} = 25 °C	-	700	-	nC
			T _{vj} = 175 °C	-	3830	-	nC
I _{rrm}	peak reverse recovery		T _{vj} = 25 °C	-	22	-	Α
current	current		T _{vj} = 175 °C	-	37	-	Α
E _{rec}	reverse recovery energy loss		T _{vj} = 25 °C	-	0.12	-	mJ
			T _{vj} = 175 °C	-	0.36	-	mJ
di _{rrf} /dt	fall rate of reverse recovery		T _{vj} = 25 °C	-	650	-	A/µs
	current		T _{vj} = 175 °C	-	760	-	A/µs

9.1. Characteristic diagrams

Table 7. Waveforms and output characteristics

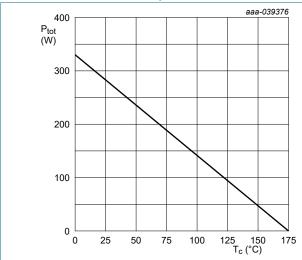
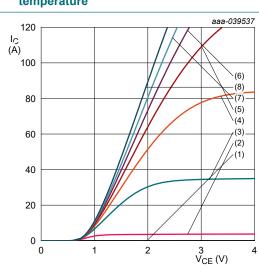


Fig. 1. Power dissipation as a function of case temperature



$$\begin{split} T_{vj} &= 25 \text{ °C} \\ &(1) \text{ V}_{GE} = 5 \text{ V} \\ &(2) \text{ V}_{GE} = 7 \text{ V} \\ &(3) \text{ V}_{GE} = 9 \text{ V} \\ &(4) \text{ V}_{GE} = 11 \text{ V} \\ &(5) \text{ V}_{GE} = 13 \text{ V} \\ &(6) \text{ V}_{GE} = 15 \text{ V} \\ &(7) \text{ V}_{GE} = 17 \text{ V} \\ &(8) \text{ V}_{GE} = 20 \text{ V} \end{split}$$

Fig. 3. Collector current as a function of collectoremitter voltage

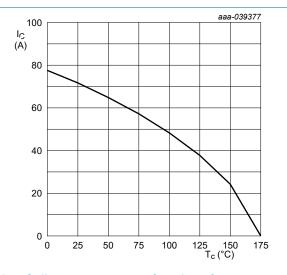
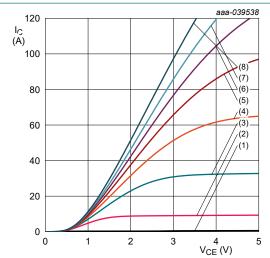
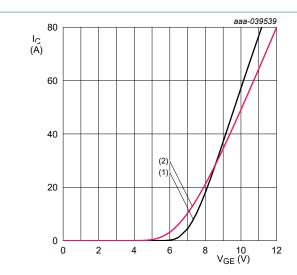


Fig. 2. Collector current as a function of case temperature



$$\begin{split} T_{vj} &= 175 \text{ °C} \\ &(1) \text{ V}_{GE} = 5 \text{ V} \\ &(2) \text{ V}_{GE} = 7 \text{ V} \\ &(3) \text{ V}_{GE} = 9 \text{ V} \\ &(4) \text{ V}_{GE} = 11 \text{ V} \\ &(5) \text{ V}_{GE} = 13 \text{ V} \\ &(6) \text{ V}_{GE} = 15 \text{ V} \\ &(7) \text{ V}_{GE} = 17 \text{ V} \\ &(8) \text{ V}_{GE} = 20 \text{ V} \end{split}$$

Fig. 4. Collector current as a function of collectoremitter voltage

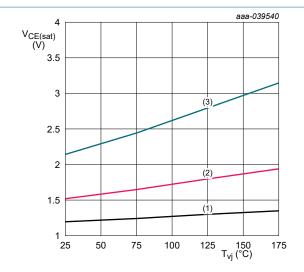


$$V_{CE} = 20 V$$

(1)
$$T_{vj} = 25 \, ^{\circ}C$$

$$(2) T_{vj} = 175 °C$$

Fig. 5. Collector current as a function of gate-emitter



$$V_{GE}$$
 = 15 V

(1)
$$I_C = 20 A$$

(2)
$$I_C = 40 A$$

$$(3) I_C = 80 A$$

Fig. 6. Collector-emitter saturation voltage as a function of junction temperature

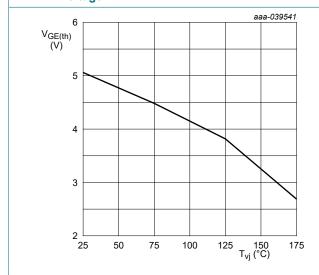
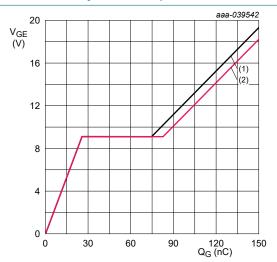


Fig. 7. Gate-emitter threshold voltage as a function of junction temperature

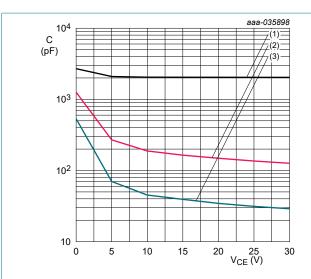


$$I_{\rm C} = 40 \, {\rm A}$$

(1)
$$V_{CE} = 130 \text{ V}$$

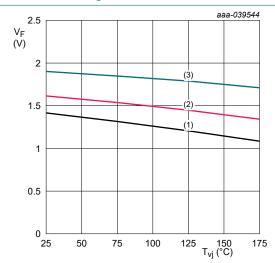
$$(2) V_{CE} = 520 V$$

Fig. 8. Gate-emitter voltage as a function of gate charge



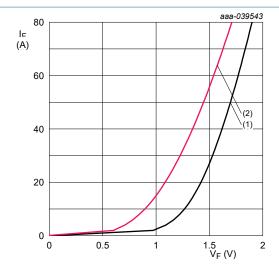
 $V_{GE} = 0 V; f = 1 MHz$

- (1) C_{ies}
- (2) Coes
- (3) Cres
- Fig. 9. Typical capacitance as a function of collectoremitter voltage



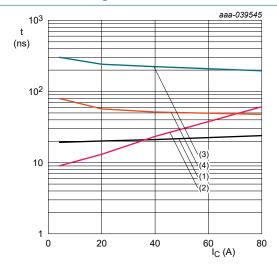
- (1) $I_F = 20 A$
- (2) $I_F = 40 \text{ A}$
- $(3) I_F = 80 A$

Fig. 11. Typical diode forward voltage as a function of junction temperature



- (1) T_{vj} = 25 °C (2) T_{vj} = 175 °C

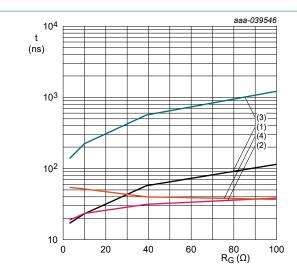
Fig. 10. Typical diode forward current as a function of forward voltage



 V_{GE} = 15 V to 0 V; V_{CC} = 400 V; $R_{G(on)}$ = 10 Ω ; $R_{G(off)} = 10 \Omega$

- (1) t_{d(on)}
- $(2) t_r$
- $(3) t_{d(off)}$
- $(4) t_f$

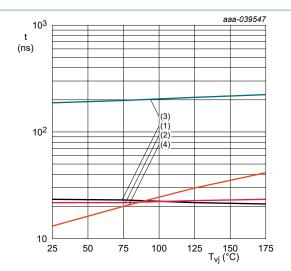
Fig. 12. Typical switching times as a function of collector current



$$V_{GE}$$
 = 15 V to 0 V; V_{CC} = 400 V; I_{C} = 40 A; T_{vj} = 175 °C

- - (1) t_{d(on)} $(2) t_r$

 - $(3) t_{d(off)}$ $(4) t_f$

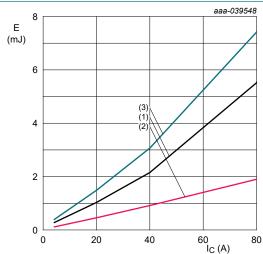


$$V_{GE}$$
 = 15 V to 0 V; I_{C} = 40 A; V_{CC} = 400 V; $R_{G(on)}$ = 10 Ω ; $R_{G(off)}$ = 10 Ω

- (1) t_{d(on)}
- $(2) t_r$
- $(3) t_{d(off)}$
- $(4) t_f$

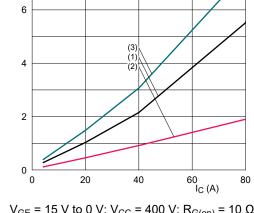
Fig. 13. Typical switching times as a function of gate resistance



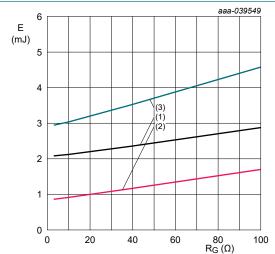


 V_{GE} = 15 V to 0 V; V_{CC} = 400 V; $R_{G(on)}$ = 10 $\Omega;$ $R_{G(off)} = 10 \Omega; T_{vi} = 175 °C$

- (1) E_{on}
- (2) E_{off}
- (3) E_{ts}



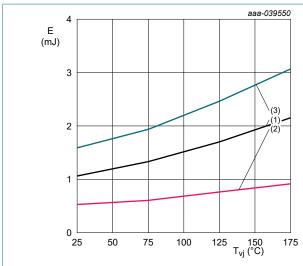
collector current



 $V_{GE} = 15 \text{ V to } 0 \text{ V}; V_{CC} = 400 \text{ V}; I_{C} = 40 \text{ A};$ $T_{vj} = 175 \,^{\circ}\text{C}$

- (1) E_{on}
- (2) E_{off}
- (3) E_{ts}

Fig. 15. Typical switching energy losses as a function of Fig. 16. Typical switching energy losses as a function of gate resistance



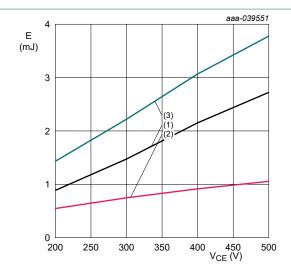
 $V_{GE} = 15 \text{ V to } 0 \text{ V}; I_{C} = 40 \text{ A}; V_{CC} = 400 \text{ V};$

 $R_{G(on)}$ = 10 Ω ; $R_{G(off)}$ = 10 Ω

(1) E_{on}

(2) E_{off}

(3) E_{ts}



 V_{GE} = 15 V to 0 V; I_{C} = 40 A; $R_{G(on)}$ = 10 Ω ;

 $R_{G(off)} = 10 \Omega; T_{vi} = 175 ^{\circ}C$

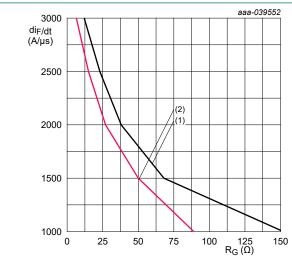
(1) E_{on}

(2) E_{off}

(3) E_{ts}

100

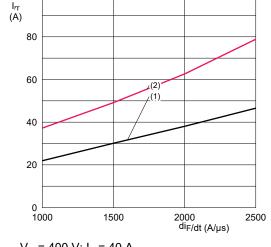
Fig. 17. Typical switching energy losses as a function of Fig. 18. Typical switching energy losses as a function of collector-emitter voltage junction temperature



 $V_R = 400 \text{ V}; I_F = 40 \text{ A}$

(1) $T_{vj} = 25 \, ^{\circ}C$

(2) $T_{vi} = 175 \,^{\circ}\text{C}$



 $V_R = 400 \text{ V}; I_F = 40 \text{ A}$

(1) $T_{vj} = 25 \, ^{\circ}C$

(2) $T_{vj} = 175 \,^{\circ}\text{C}$

Fig. 20. Typical reverse recovery current as a function of rate of change of forward current

Fig. 19. Typical rate of change of forward current as a function of gate resistance

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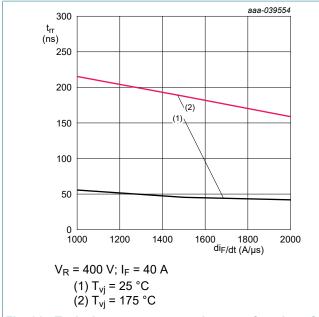
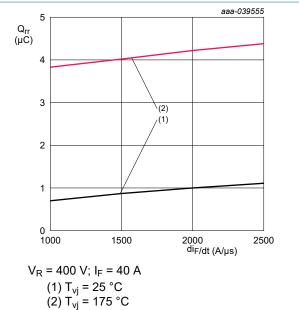
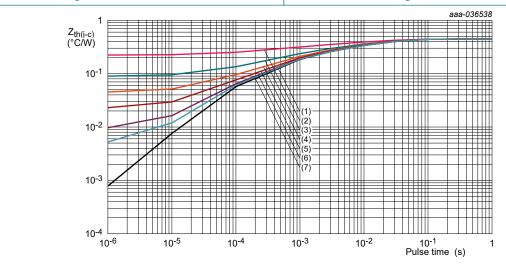


Fig. 21. Typical reverse recovery time as a function of rate of change of forward current



(2) $T_{vj} = 175 \,^{\circ}\text{C}$

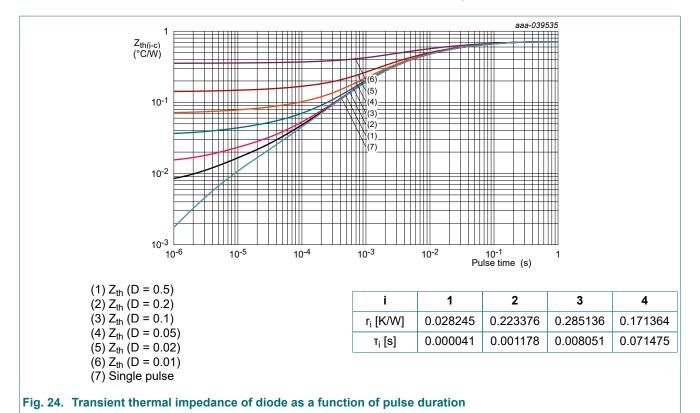
Fig. 22. Typical reverse recovery charge as a function of rate of change of forward current



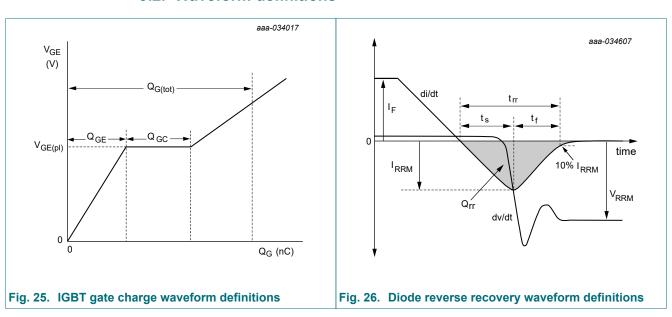
- (1) Z_{th} (D = 0.5)
- (2) Z_{th} (D = 0.2)
- (3) Z_{th} (D = 0.1)
- (4) Z_{th} (D = 0.05)
- $(5) Z_{th} (D = 0.02)$ (6) Z_{th} (D = 0.01)
- (7) Single pulse

2 i 1 3 4 $r_i [K/W]$ 0.056786 0.123135 0.144927 0.121162 0.000113 0.000681 0.005543 0.036756 $T_i\left[S\right]$

Fig. 23. Transient thermal impedance of IGBT as a function of pulse duration



9.2. Waveform definitions



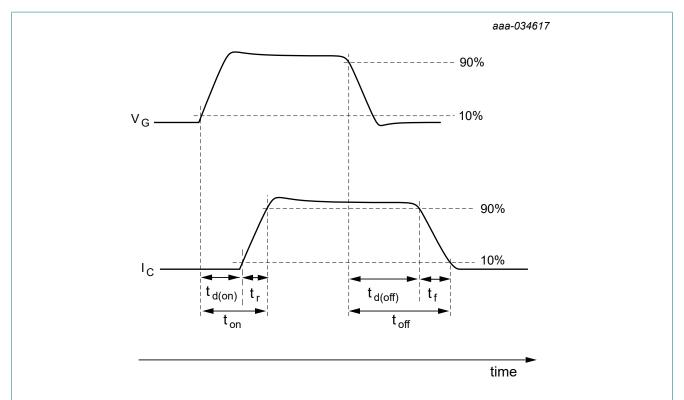
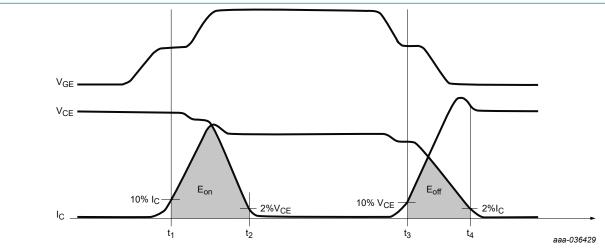


Fig. 27. IGBT switching times definitions



$$E_{\text{on}} = {}^{t_2}V_{\text{CE}} I_C dt$$

$$E_{\text{on}} = {}^{t_2}_{t_1} V_{\text{CE}} I_C dt$$

$$E_{\text{off}} = {}^{t_4}_{t_3} V_{\text{CE}} I_C dt$$

Fig. 28. IGBT switching energy loss definitions

10. Package outline

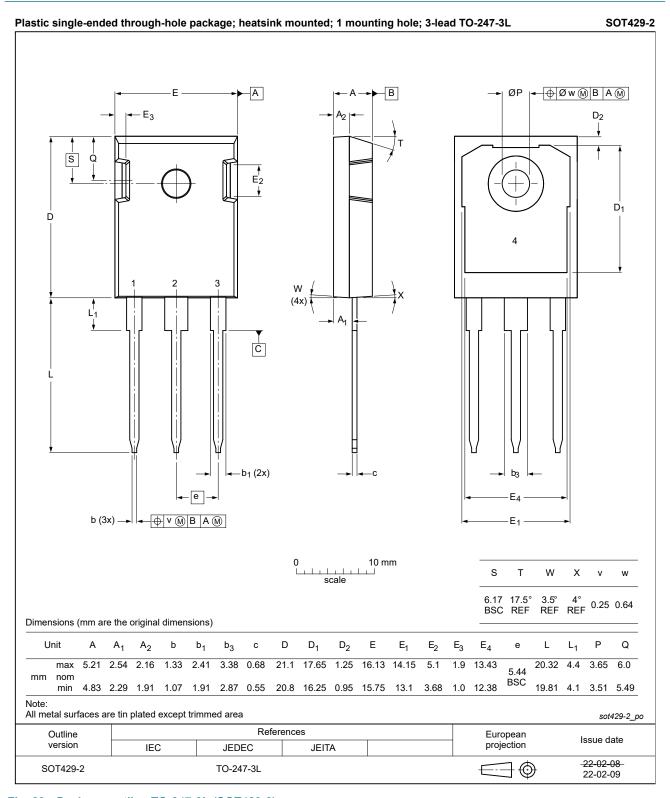


Fig. 29. Package outline TO-247-3L (SOT429-2)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
NGW40T65M3DFP v. 1.1	20250228	Product data sheet	-	-			
Modifications:	 Naming conve 	Naming conventions brought into alignment with other data sheets					
NGW40T65M3DFP v. 1	20240628	Product data sheet	-	-			

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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